BYV30MW-650PT2

Ultrafast power diode

Rev.01 - 27 November 2023 Product data sheet

1. General description

Ultrafast power diode in a 2-lead TO247 plastic package

2. Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Power Factor Correction (PFC)

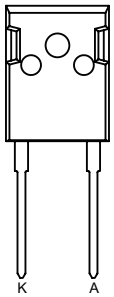
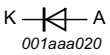
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage			650			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_{mb} \leq 134$ °C; Fig. 1; Fig. 2; Fig. 3		30			A
I_{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \leq 134$ °C; square-wave pulse		60			A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		350			A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		385			A
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
V_F	forward voltage	I_F = 30 A; T_j = 25 °C; Fig. 6		-	1.34	1.55	V
		I_F = 30 A; T_j = 150 °C; Fig. 6		-	1.06	1.27	V
Dynamic characteristics							
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T_j = 25 °C; Fig. 7		-	27	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO247-2L	 *001aaa020*
2	A	anode		
mb	mb	mounting base; connected to cathod		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV30MW-650PT2	TO247-2L	BYV30MW-650PT2Q	Tube	30	TO247L-2L	10-Nov-2020

7. Marking

Table 4. Marking codes

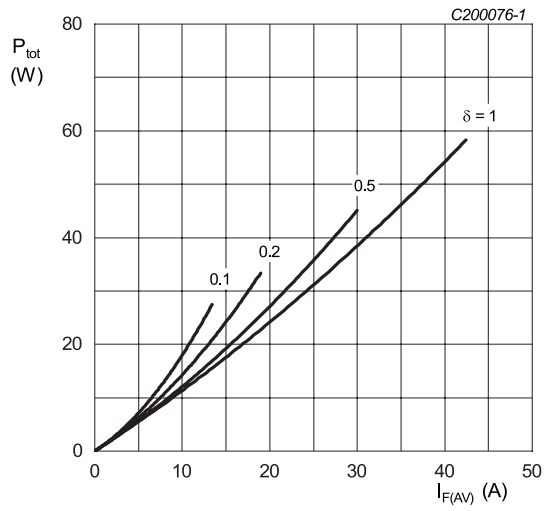
Type number	Marking codes
BYV30MW-650PT2	BYV30MW 650PT2

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

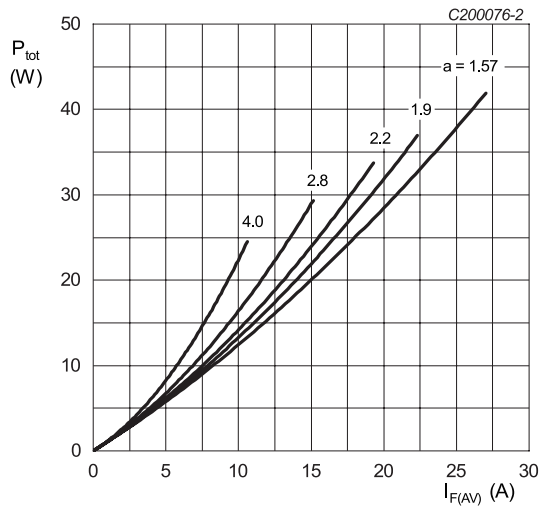
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_{mb} \leq 134$ °C; Fig. 1; Fig. 2; Fig. 3		30	A
I_{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_{mb} \leq 134$ °C; square-wave pulse		60	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		350	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		385	A
T_{stg}	storage temperature			-65 to 175	°C
T_j	junction temperature			-65 to 175	°C



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

V_o = 1.061 V; R_s = 0.0074 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)} / I_{F(AV)}$

V_o = 1.061 V; R_s = 0.0074 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

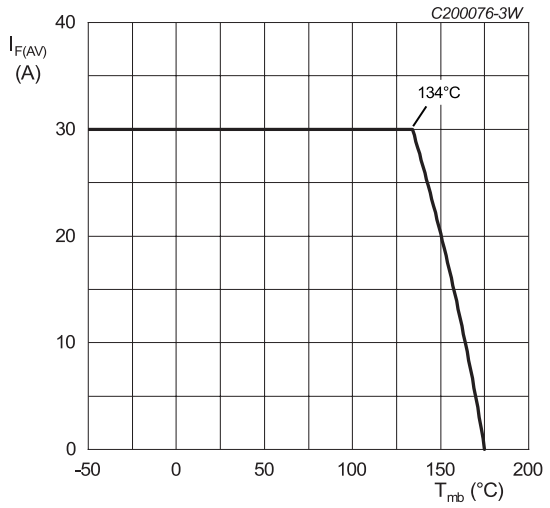


Fig. 3. Forward current as a function of mounting base temperature; maximum values

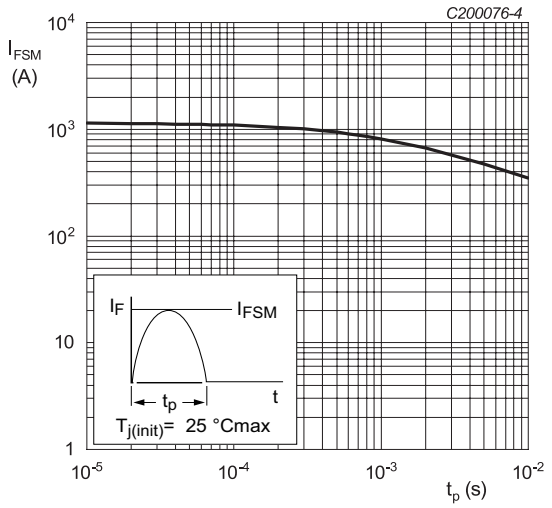


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	0.91	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

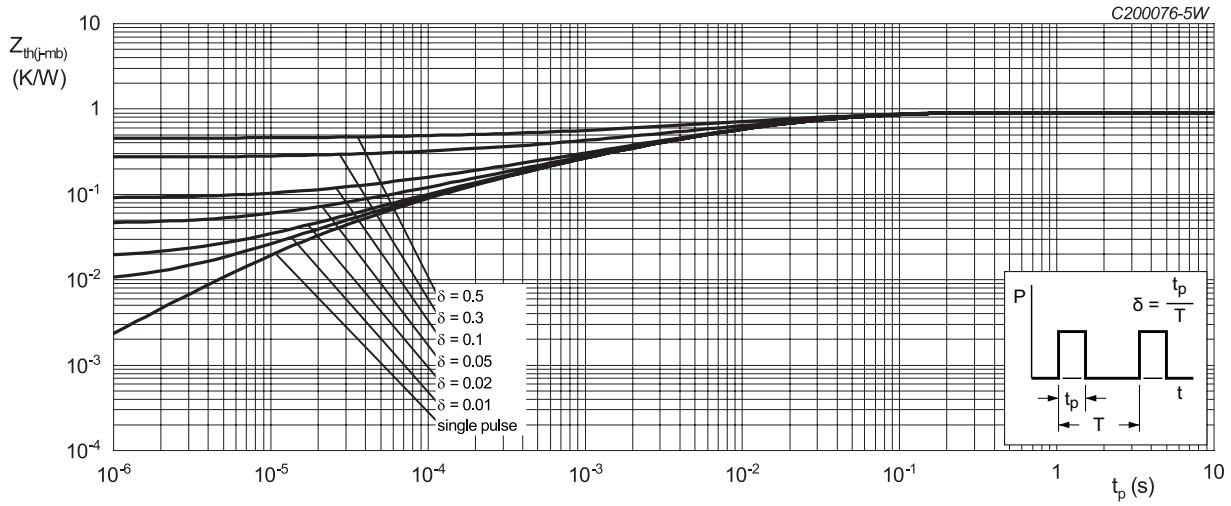
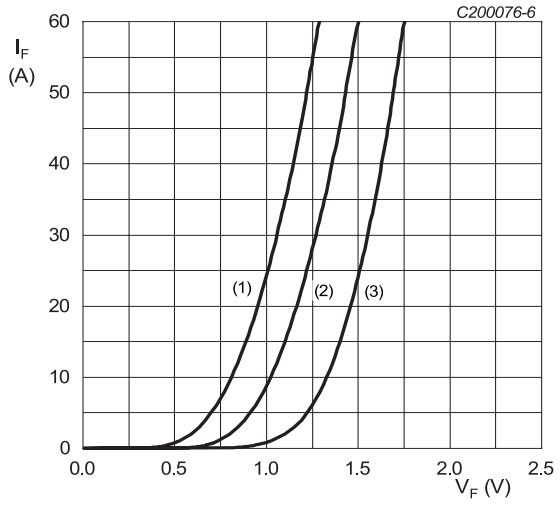


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V_F	forward voltage	I_F = 30 A; T_j = 25 °C; Fig. 6		-	1.34	1.55	V
		I_F = 30 A; T_j = 150 °C; Fig. 6		-	1.06	1.27	V
I_R	reverse current	V_R = 650 V; T_j = 25 °C		-	0.67	30	µA
		V_R = 650 V; T_j = 150 °C		-	-	1	mA
Dynamic characteristics							
Q_r	reverse charge	I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	159.3	-	nC
		I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 125 °C; Fig. 7		-	599.3	-	nC
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T_j = 25 °C; Fig. 7		-	27	-	ns
		I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	78	-	ns
		I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 125 °C; Fig. 7		-	133	-	ns
I_{RM}	peak reverse recovery current	I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	4.1	-	A
		I_F = 30 A; V_R = 400 V; dI_F/dt = 100 A/µs; T_j = 125 °C; Fig. 7		-	9.1	-	A
E_{as}	non-repetitive avalanche energy	$T_{j(init)}$ = 25 °C		30	-	-	mJ



V_o = 1.061 V; R_s = 0.0074 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

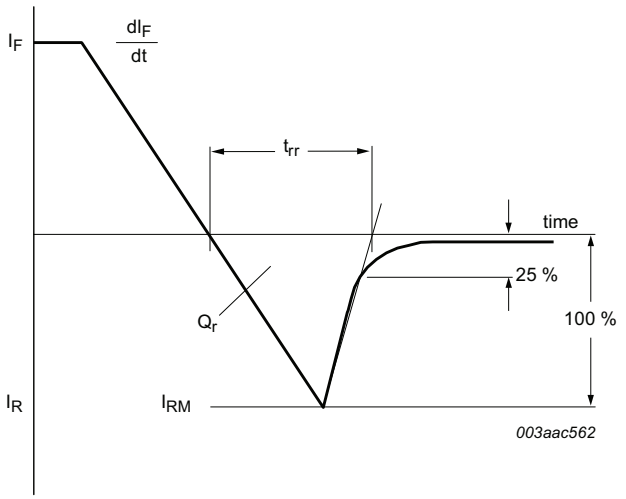
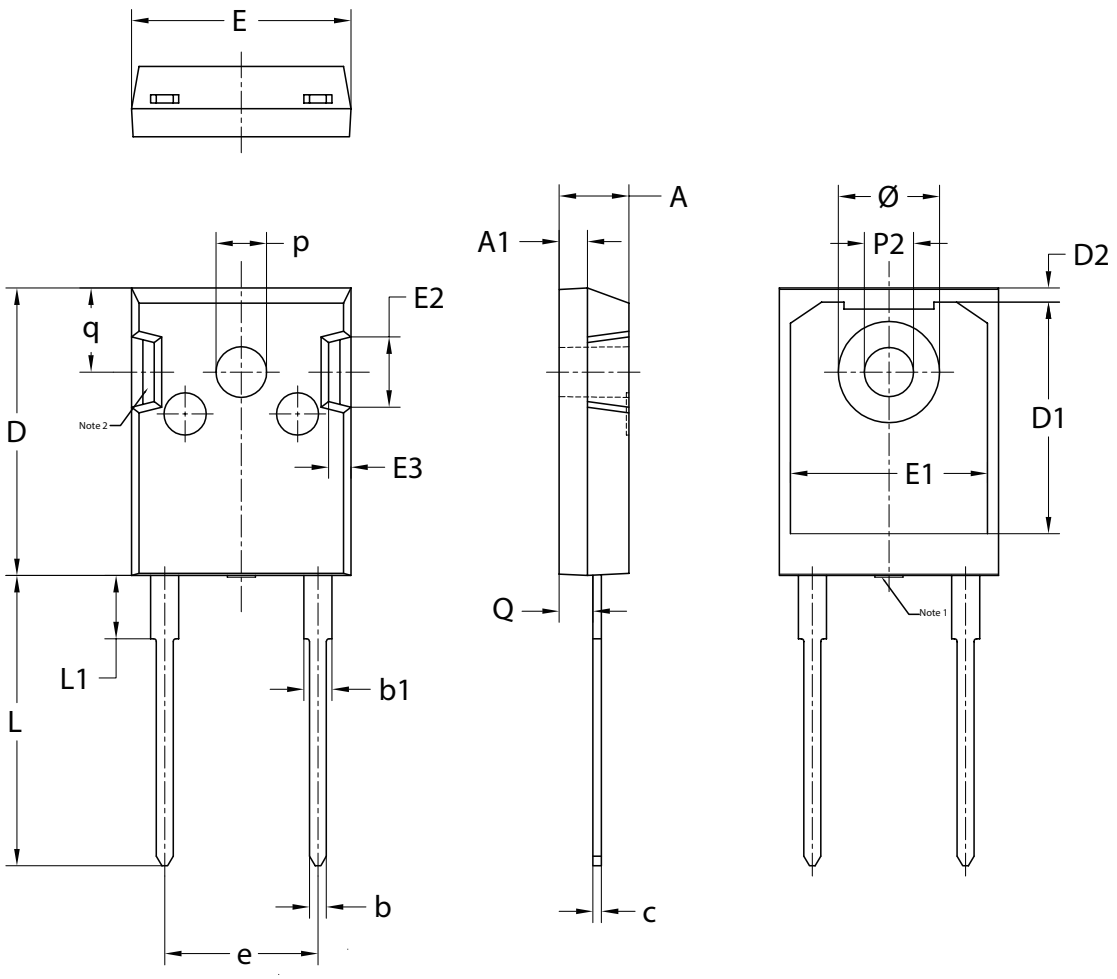


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline

Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 2 leads TO-247 TO247-2L



UNIT	A	A_1	b	b_1	c	D	D_1 (2)	D_2	E	E_1	E_2	E_3	e	L	L_1	P_2	p	Q	q	Ø
mm	5.20 4.70	2.10 1.90	1.40 1.00	2.20 1.80	0.70 0.50	20.60 20.30	16.20 16.87	1.20 0.80	15.75 15.45	14.22 13.82	5.20 4.80	1.80 1.40	10.90 BSC	20.72 20.22	4.75 4.25	3.60 3.40	3.70 3.50	2.60 2.20	6.18 5.78	7.30 7.10

Note:
1. Mold resin protrusion max 0.127mm.
2. Metal exposed with Sn plating.

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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